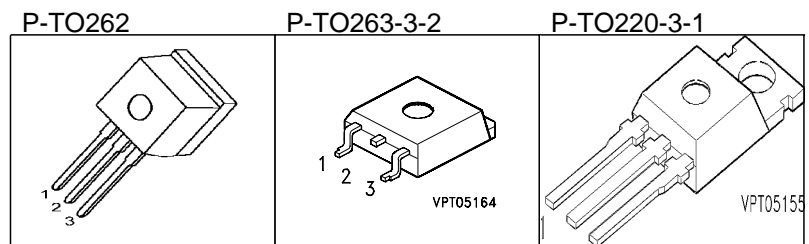


## Cool MOS™ Power Transistor

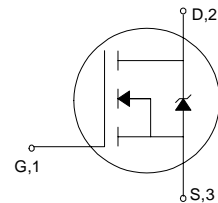
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- Optimized capacitances
- Improved noise immunity

### Product Summary

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	0.6	$\Omega$
$I_D$	7.3	A



Type	Package	Ordering Code	Marking
SPP07N60S5	P-TO220-3-1	Q67040-S4172	07N60S5
SPB07N60S5	P-TO263-3-2	Q67040-S4185	07N60S5
SPI07N60S5	P-TO262	Q67040-S4328	07N60S5



### Maximum Ratings, at $T_C = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	$I_D$		A
$T_C=25^\circ\text{C}$		7.3	
$T_C=100^\circ\text{C}$		4.6	
Pulsed drain current <sup>1)</sup>	$I_{D \text{ puls}}$	14.6	
$T_C=25^\circ\text{C}$			
Avalanche energy, single pulse	$E_{AS}$	230	mJ
$I_D = 5.5 \text{ A}, V_{DD} = 50 \text{ V}$			
Avalanche energy (repetitive, limited by $T_{jmax}$ )	$E_{AR}$	0.5	
$I_D = 7.3 \text{ A}, V_{DD} = 50 \text{ V}$			
Avalanche current (repetitive, limited by $T_{jmax}$ )	$I_{AR}$	7.3	A
Reverse diode $dv/dt$	$dv/dt$	6	kV/ $\mu\text{s}$
$I_S=7.3\text{A}, V_{DS}<V_{DSS}, di/dt=100\text{A}/\mu\text{s}, T_{jmax}=150^\circ\text{C}$			
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation	$P_{tot}$	83	W
$T_C=25^\circ\text{C}$			
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$

**Electrical Characteristics**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Thermal Characteristics**

Thermal resistance, junction - case	$R_{thJC}$	-	-	1.5	K/W
Thermal resistance, junction - ambient (Leaded and through-hole packages)	$R_{thJA}$	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	62	
		-	35	-	

**Static Characteristics**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Drain-source breakdown voltage $V_{GS} = 0\text{ V}$ , $I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	600	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 350\text{ }\mu\text{A}$ , $T_j = 25\text{ °C}$	$V_{GS(th)}$	3.5	4.5	5.5	
Zero gate voltage drain current, $V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$ , $T_j = 25\text{ °C}$ $V_{GS} = 0\text{ V}$ , $T_j = 150\text{ °C}$	$I_{DSS}$	-	0.5	1	$\mu\text{A}$
		-	-	100	
Gate-source leakage current $V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	-	-	100	nA
Drain-source on-state resistance $V_{GS} = 10\text{ V}$ , $I_D = 4.6\text{ A}$	$R_{DS(on)}$	-	0.54	0.6	$\Omega$

<sup>1</sup> current limited by  $T_{jmax}$

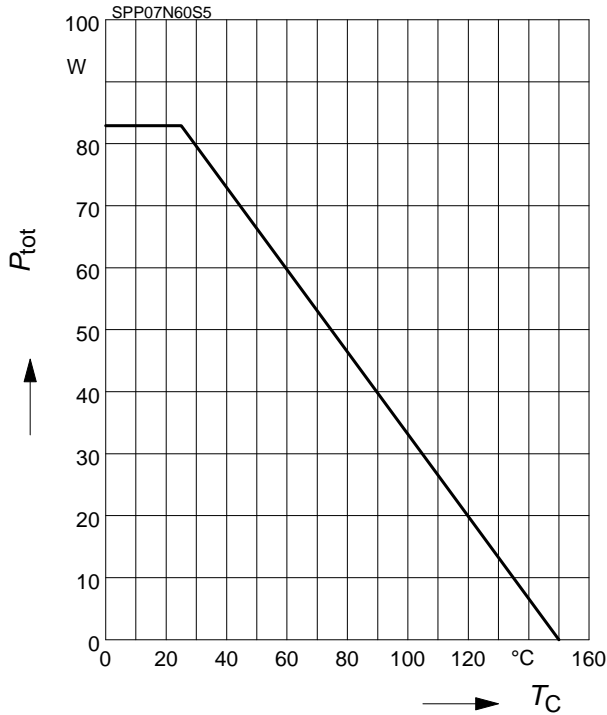
<sup>2</sup> Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Dynamic Characteristics</b>						
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 4.6\text{A}$	-	4	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	970	-	pF
Output capacitance	$C_{oss}$		-	370	-	
Reverse transfer capacitance	$C_{rss}$		-	10	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350\text{V}$ , $V_{GS} = 10\text{V}$ , $I_D = 7.3\text{A}$ , $R_G = 12\Omega$	-	120	-	ns
Rise time	$t_r$		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	170	255	
Fall time	$t_f$		-	20	30	
<b>Gate Charge Characteristics</b>						
Gate to source charge	$Q_{gs}$	$V_{DD} = 350\text{V}$ , $I_D = 7.3\text{A}$	-	7.5	-	nC
Gate to drain charge	$Q_{gd}$		-	16.5	-	
Total gate charge	$Q_g$	$V_{DD} = 350\text{V}$ , $I_D = 7.3\text{A}$ , $V_{GS} = 0$ to $10\text{V}$	-	27	35	
<b>Reverse Diode</b>						
Inverse diode continuous forward current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	-	-	7.3	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	14.6	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0\text{V}$ , $I_F = 7.3\text{A}$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R = 350\text{V}$ , $I_F = I_S$ , $di_F/dt = 100\text{A}/\mu\text{s}$	-	750	1275	ns
Reverse recovery charge	$Q_{rr}$		-	4.9	-	$\mu\text{C}$

**Power dissipation**

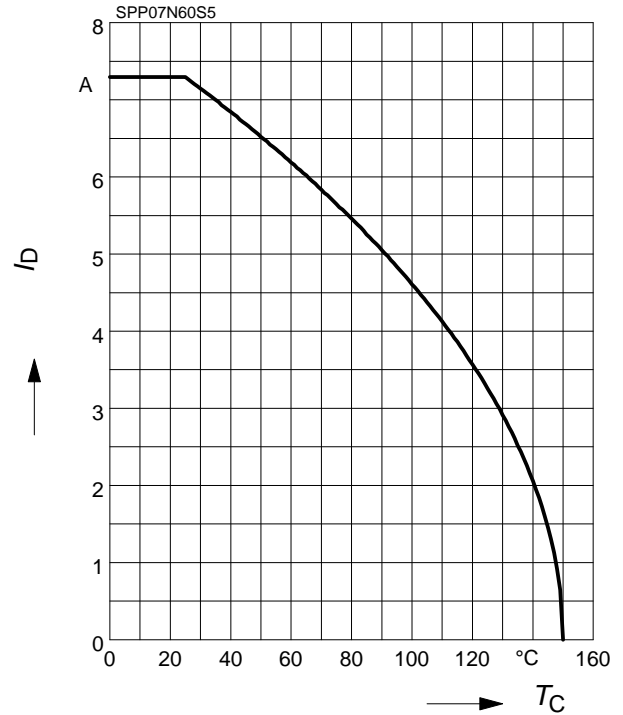
$P_{tot} = f(T_C)$



**Drain current**

$I_D = f(T_C)$

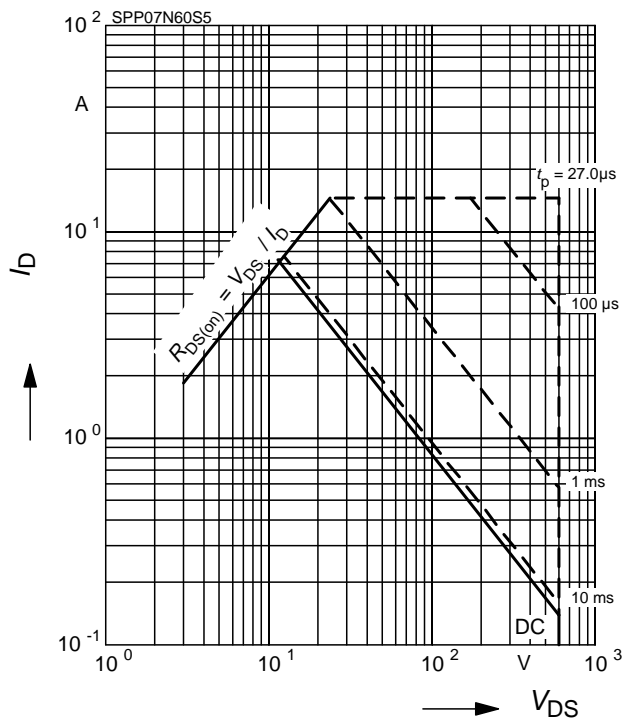
parameter:  $V_{GS} \geq 10\text{ V}$



**Safe operating area**

$I_D = f(V_{DS})$

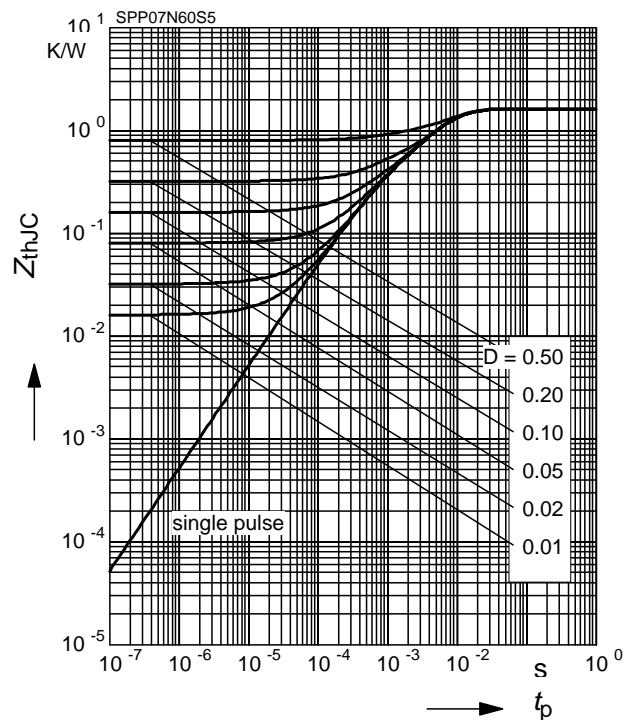
parameter:  $D=0.01, T_C=25^\circ\text{C}$



**Transient thermal impedance**

$Z_{thJC} = f(t_p)$

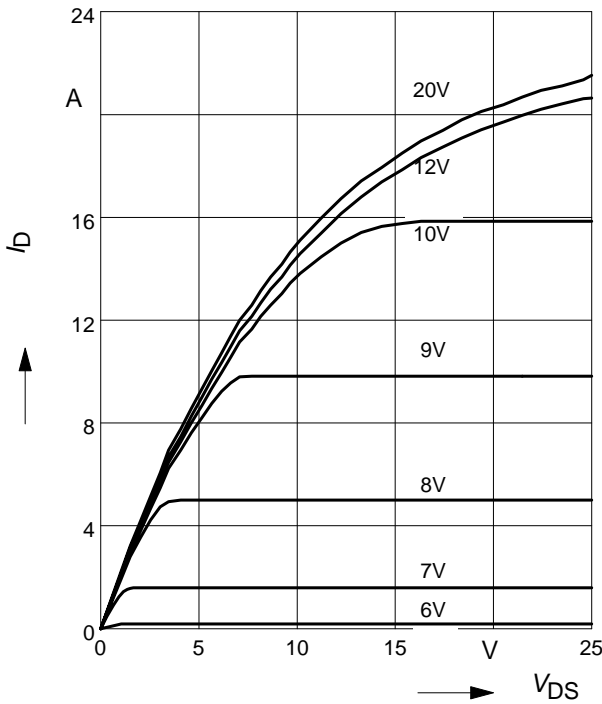
parameter:  $D = t_p/T$



**Typ. output characteristic**

$I_D = f(V_{DS})$

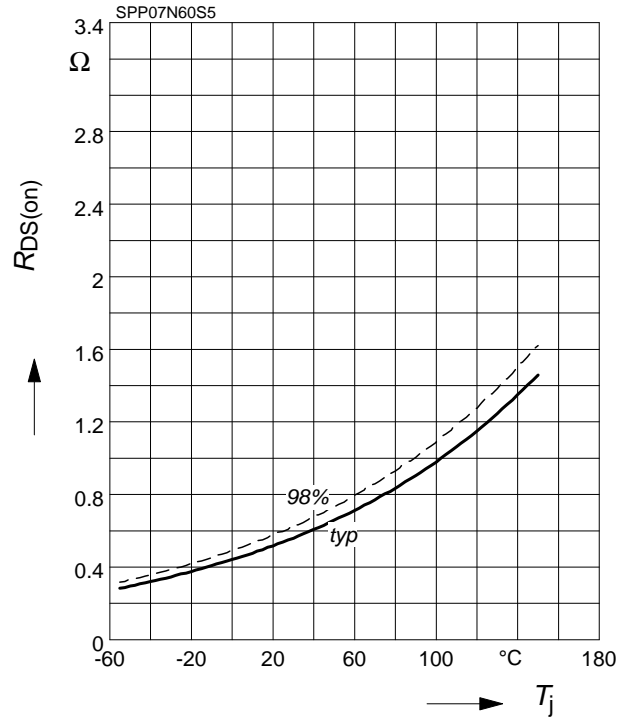
Parameter:  $V_{GS}, T_j = 25\text{ }^\circ\text{C}$



**Drain-source on-resistance**

$R_{DS(on)} = f(T_j)$

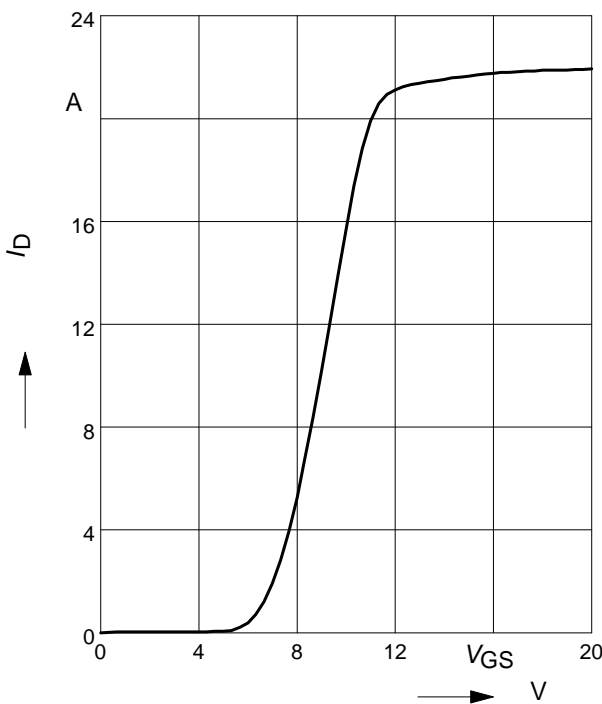
parameter :  $I_D = 4.6\text{ A}, V_{GS} = 10\text{ V}$



**Typ. transfer characteristics**

$I_D = f(V_{GS})$

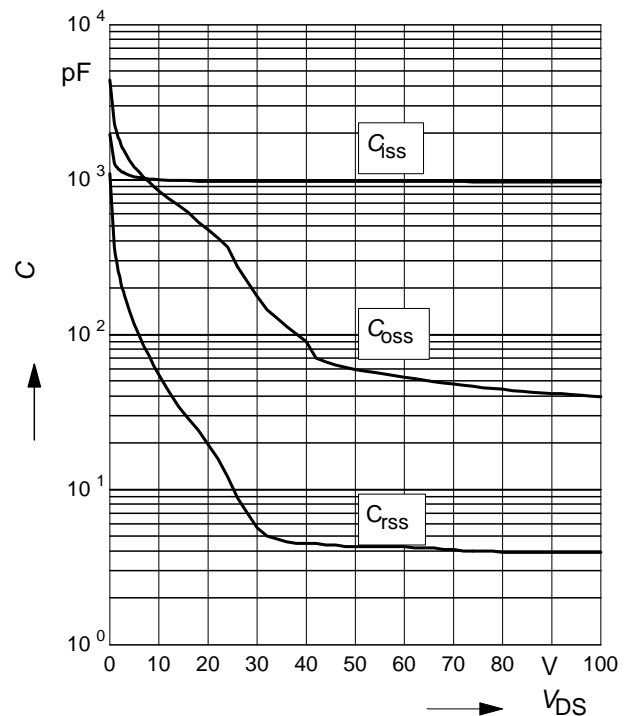
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



**Typ. capacitances**

$C = f(V_{DS})$

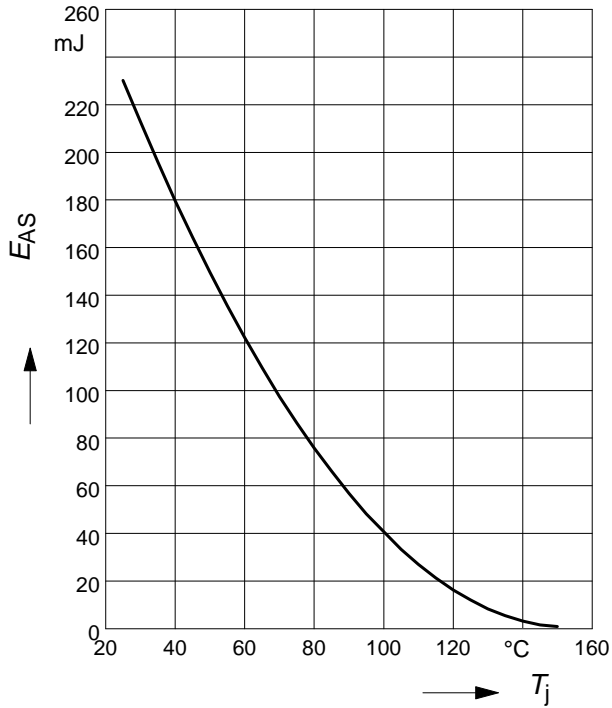
parameter:  $V_{GS} = 0\text{ V}, f = 1\text{ MHz}$



**Avalanche energy**

$$E_{AS} = f(T_j)$$

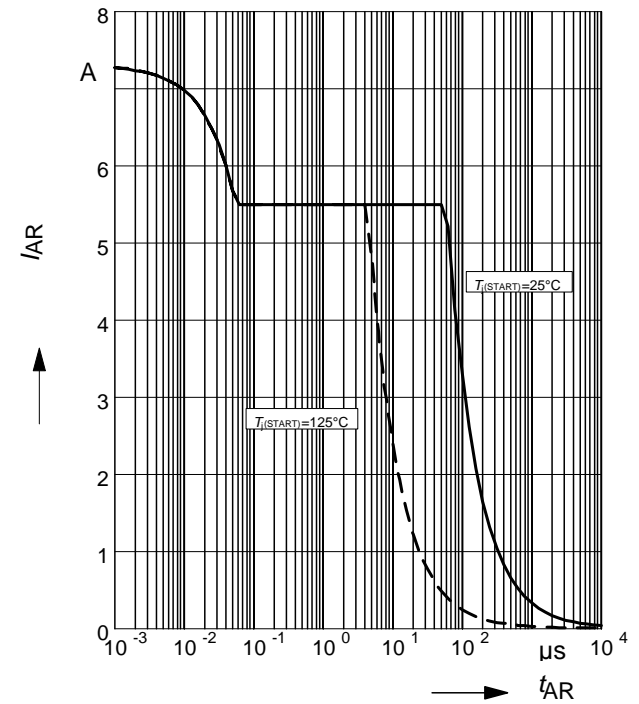
par.:  $I_D = 5.5A, V_{DD} = 50V$



**Avalanche SOA**

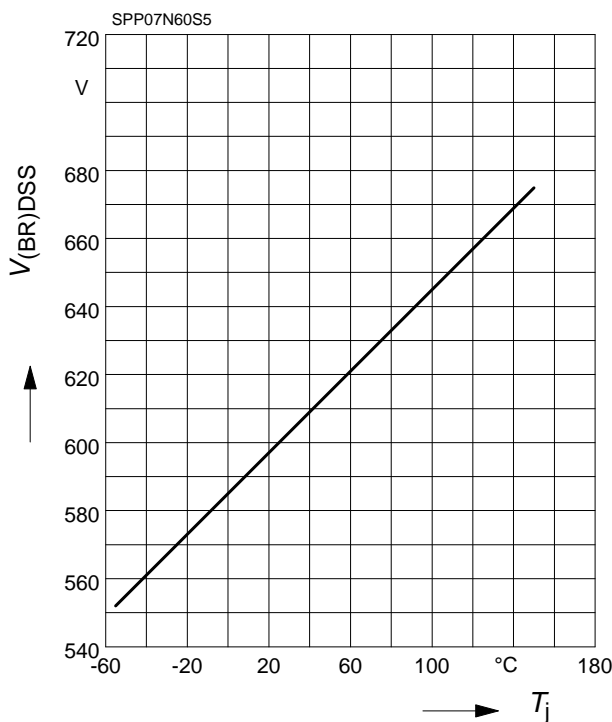
$$I_{AR} = f(t_{AR})$$

par.:  $T_j \leq 150\text{ °C}$



**Drain-source breakdown voltage**

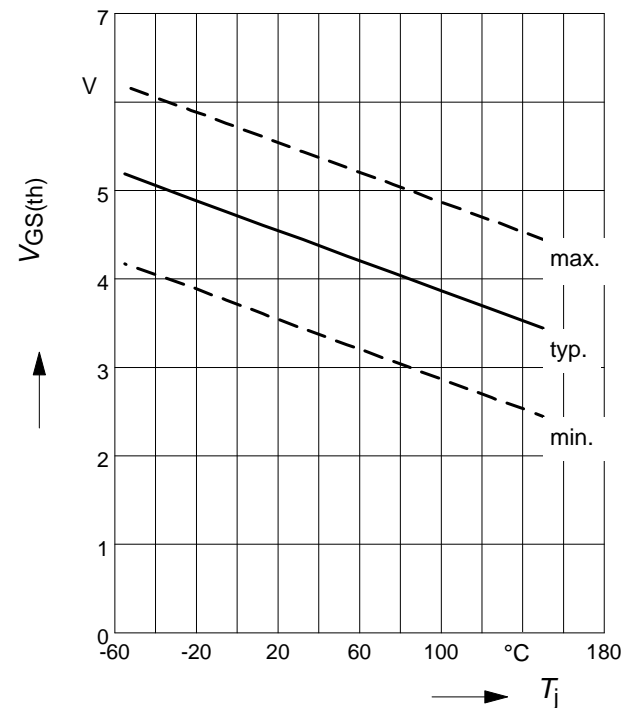
$$V_{(BR)DSS} = f(T_j)$$



**Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

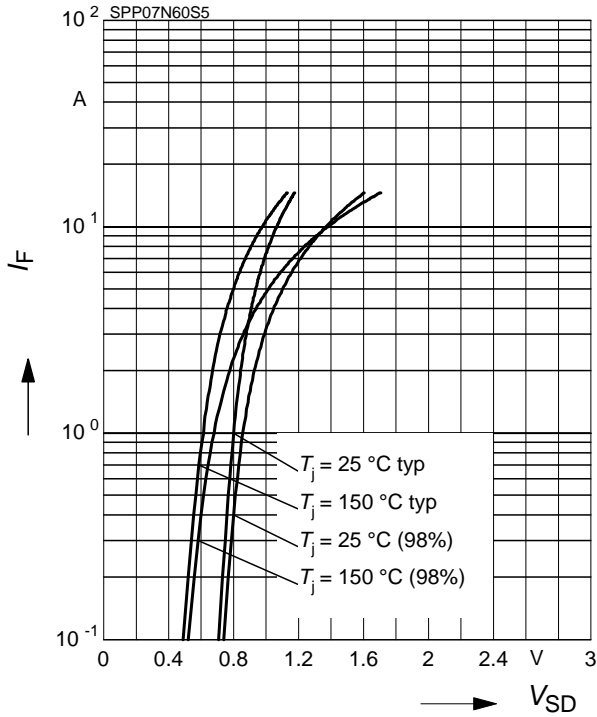
parameter:  $V_{GS} = V_{DS}, I_D = 350\text{ }\mu A$



**Forward characteristics of reverse diode**

$$I_F = f(V_{SD})$$

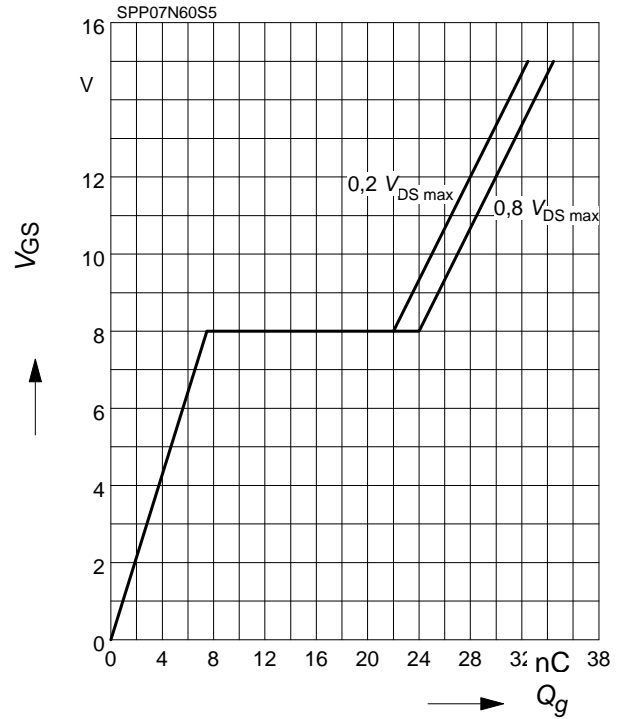
parameter:  $T_j$ ,  $t_p = 10 \mu s$



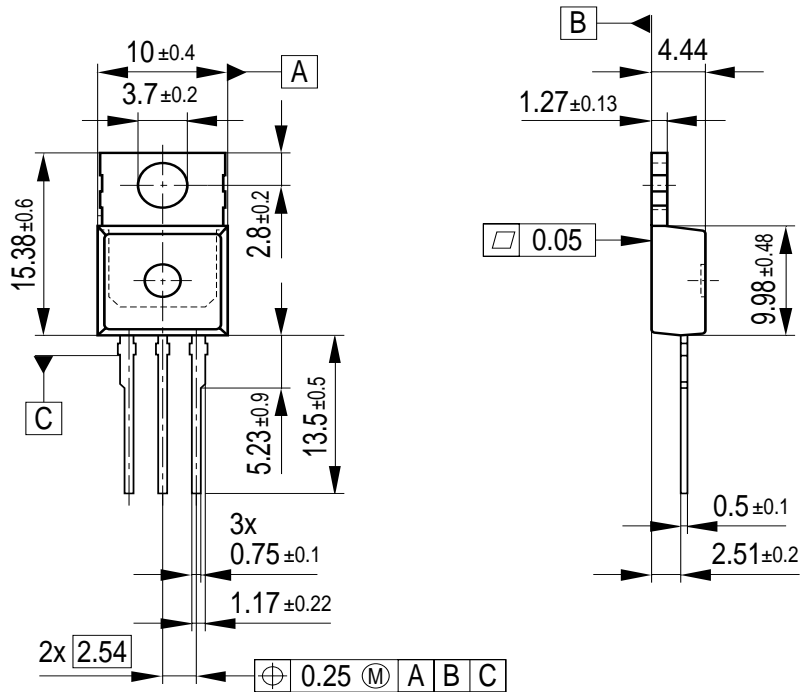
**Typ. gate charge**

$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = 7.3 \text{ A pulsed}$

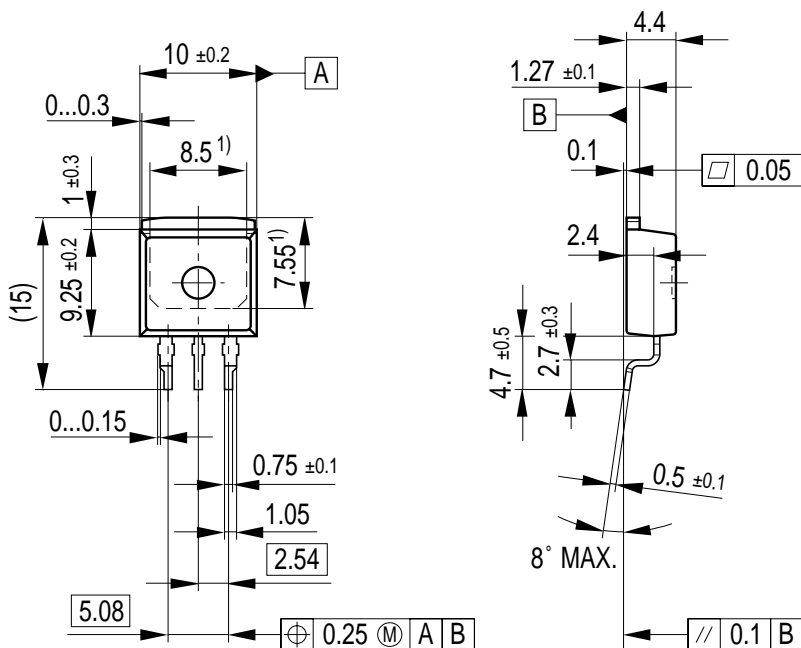


P-TO-220-3-1



All metal surfaces tin plated, except area of cut.  
Metal surface min. x=7.25, y=12.3

P-TO-263-3-1 (D<sup>2</sup>-PAK)

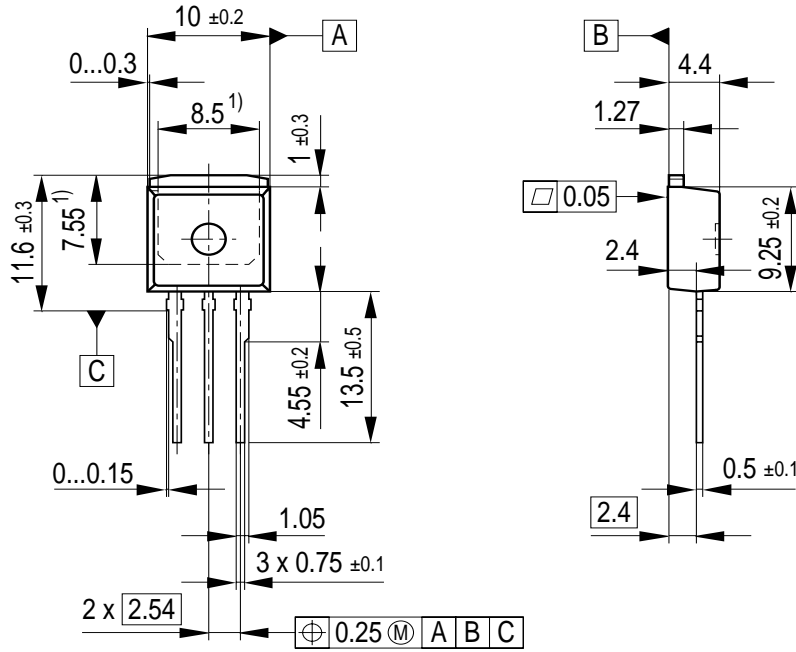


<sup>1)</sup> Typical

All metal surfaces: tin plated, except area of cut.  
Metal surface min. x=7.25, y=6.9



P-TO-262-3-1 (I<sup>2</sup>-PAK)



<sup>1)</sup> Typical

Metal surface min. X = 7.25, Y = 6.9

All metal surfaces tin plated, except area of cut.

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